

Jiancheng Yang

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

21
papers

1,937
citations

17
h-index

21
g-index

21
ext. papers

2,441
ext. citations

3.5
avg, IF

5.14
L-index

#	Paper	IF	Citations
21	Radiation damage effects in Ga ₂ O ₃ materials and devices. <i>Journal of Materials Chemistry C</i> , 2019 , 7, 10-24	7.1	90
20	Electron injection-induced effects in Si-doped β -Ga ₂ O ₃ . <i>AIP Advances</i> , 2019 , 9, 015127	1.5	11
19	Switching Behavior and Forward Bias Degradation of 700V, 0.2A, β -Ga ₂ O ₃ Vertical Geometry Rectifiers. <i>ECS Journal of Solid State Science and Technology</i> , 2019 , 8, Q3028-Q3033	2	12
18	Implementation of a 900V Switching Circuit for High Breakdown Voltage β -Ga ₂ O ₃ Schottky Diodes. <i>ECS Journal of Solid State Science and Technology</i> , 2019 , 8, Q3229-Q3234	2	7
17	Vertical geometry 33.2 A, 4.8 MW cm ² Ga ₂ O ₃ field-plated Schottky rectifier arrays. <i>Applied Physics Letters</i> , 2019 , 114, 232106	3.4	26
16	Reverse Breakdown in Large Area, Field-Plated, Vertical β -Ga ₂ O ₃ Rectifiers. <i>ECS Journal of Solid State Science and Technology</i> , 2019 , 8, Q3159-Q3164	2	16
15	Dynamic Switching Characteristics of 1 A Forward Current β -Ga ₂ O ₃ Rectifiers. <i>IEEE Journal of the Electron Devices Society</i> , 2019 , 7, 57-61	2.3	20
14	Point defect induced degradation of electrical properties of Ga ₂ O ₃ by 10 MeV proton damage. <i>Applied Physics Letters</i> , 2018 , 112, 032107	3.4	72
13	A review of Ga ₂ O ₃ materials, processing, and devices. <i>Applied Physics Reviews</i> , 2018 , 5, 011301	17.3	1114
12	Effect of 1.5 MeV electron irradiation on β -Ga ₂ O ₃ carrier lifetime and diffusion length. <i>Applied Physics Letters</i> , 2018 , 112, 082104	3.4	37
11	Zika virus detection using antibody-immobilized disposable cover glass and AlGa _N /Ga _N high electron mobility transistors. <i>Applied Physics Letters</i> , 2018 , 113, 032101	3.4	18
10	Diffusion length of non-equilibrium minority charge carriers in β -Ga ₂ O ₃ measured by electron beam induced current. <i>Journal of Applied Physics</i> , 2018 , 123, 185704	2.5	37
9	Ga ₂ O ₃ Schottky rectifiers with 1 ampere forward current, 650 V reverse breakdown and 26.5 MW.cm ⁻² figure-of-merit. <i>AIP Advances</i> , 2018 , 8, 055026	1.5	51
8	Vertical Geometry, 2-A Forward Current Ga ₂ O ₃ Schottky Rectifiers on Bulk Ga ₂ O ₃ Substrates. <i>IEEE Transactions on Electron Devices</i> , 2018 , 65, 2790-2796	2.9	30
7	Effect of surface treatments on electrical properties of β -Ga ₂ O ₃ . <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2018 , 36, 061201	1.3	30
6	Defects responsible for charge carrier removal and correlation with deep level introduction in irradiated β -Ga ₂ O ₃ . <i>Applied Physics Letters</i> , 2018 , 113, 092102	3.4	46
5	High reverse breakdown voltage Schottky rectifiers without edge termination on Ga ₂ O ₃ . <i>Applied Physics Letters</i> , 2017 , 110, 192101	3.4	118

4	High Breakdown Voltage (001) β -Ga ₂ O ₃ Schottky Rectifiers. <i>IEEE Electron Device Letters</i> , 2017 , 38, 906-909	4.4	114
3	Inductively coupled plasma etch damage in (-201) Ga ₂ O ₃ Schottky diodes. <i>Applied Physics Letters</i> , 2017 , 110, 142101	3.4	37
2	Ohmic contacts on n-type β -Ga ₂ O ₃ using AZO/Ti/Au. <i>AIP Advances</i> , 2017 , 7, 095313	1.5	32
1	Rapid detection of cardiac troponin I using antibody-immobilized gate-pulsed AlGa _N /Ga _N high electron mobility transistor structures. <i>Applied Physics Letters</i> , 2017 , 111, 202104	3.4	19